

L Number	Hits	Search Text	DB	Time stamp
1	0	438/240,250,253,393,399.pn. and (Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (tantalum adj pentamethoxide or tantalum adj pentaethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/27 15:37
2	0	438/240,250,253,393,399.pn. and (Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (tantalum adj pentamethoxide or tantalum adj pentaethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/27 15:38
-	15673	(Ta or tantalum) and CVD	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:04
-	897	(Ta or tantalum) and CVD and (capacitor) and (precursor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/26 15:23
-	102	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/26 15:27
-	96	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/30 16:08
-	30822	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) (lower adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/26 15:28
-	21	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (lower adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/26 15:28
-	12	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (lower adj electrode) and (upper adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 16:44
-	12	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (lower adj electrode) and (upper adj electrode) and (substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/26 15:32
-	0	6207489.pn. and purging	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:06
-	2	6207489.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:38
-	2	20020100959.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:25
-	0	20020100959.pn. and (purge or purging)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:26
-	0	20020100959.pn. and (purge or purging or exhaust)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:27
-	0	6207489.pn. and (purge or purging or exhaust)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:28

-	0	6218260.pn. and (purge or purging or exhaust)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 09:29
-	2	20020006708.pn. and (purge or purging or exhaust)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:50
-	9	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (lower adj electrode) and (upper adj electrode) and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 16:57
-	1	6376299.pn. and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:00
-	2	6482740.pn. and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:08
-	1	6376299.pn. and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:17
-	0	6376299.pn. and (Ru or Pt or Ir.) and (purge or purging or exhaust)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:16
-	1	20020006708.pn. and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:01
-	1	20020100959.pn. and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:28
-	0	20020100959.pn. and (Ru or Pt or Ir.) and (purge or purging)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:29
-	1	20020100959.pn. and (Ru or Pt or Ir.) and (flow adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:30
-	0	6372598.pn. and (Ru or Pt or Ir.) and (flow adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:30
-	1	6372598.pn. and (Ru or Pt or Ir.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:31
-	1	20020006708.pn. and (titanium adj nitride or tantalum adj nitride or tungsten adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:57
-	1	20020006708.pn. and (titanium adj nitride or tantalum adj nitride or tungsten adj nitride) and (precursor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/27 17:58
-	1	20020006708.pn. and (Ru or Pt or Ir.) and (bottom or lower adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:13
-	1	20020006708.pn. and (argon or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 15:54

-	0	20020006708.pn. and (sccm)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:16
-	1	20020006708.pn. and (flow )	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:27
-	0	20020006708.pn. and (flow adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:27
-	0	20020006708.pn. and (sccm)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:28
-	1	20020006708.pn. and (flow)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:32
-	0	20020006708.pn. and (cubic adj centimeters)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:33
-	2	6207489.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:38
-	1	6207489.pn. and flow	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:41
-	0	6207489.pn. and sccm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:42
-	1	6207489.pn. and flow adj rate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:42
-	96	438/240,250,253,393,399(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 15:45
-	1	20020006708.pn. and (chemical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 16:58
-	156	atomic adj layer adj deposition and (atomic adj layer adj epitax\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 17:24
-	0	(atomic adj layer adj deposition and (atomic adj layer adj epitax\$3)) near dielectric adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 17:28
-	0	(atomic adj layer adj deposition and (atomic adj layer adj epitax\$3)) with dielectric adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 17:28
-	0	(atomic adj layer adj deposition and (atomic adj layer adj epitax\$3)) near12 dielectric adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 17:29
-	0	atomic adj layer adj deposition and atomic adj layer adj epitax\$3 and dielectric adj insulat\$3 and international adj business adj machines	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 17:30
-	6	atomic adj layer adj deposition and atomic adj layer adj epitax\$3 and dielectric adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 19:06

-	1	6203613.pn. and CVD	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 19:09
-	0	6203613.pn. and compacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 19:10
-	2	6203613.pn. and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/17 19:10
-	1	20020006708.pn. and Ru	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/22 16:28
-	0	6207489.pn. and (tantalum adj pentamethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 10:48
-	2	(tantalum adj pentamethoxide) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:14
-	0	(tantalum adj pentamethoxide) and capacitor and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:18
-	38	(tantalum adj ethylate) and capacitor and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:20
-	23	(tantalum adj ethylate) and capacitor and electrode and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:20
-	23	(tantalum adj ethylate) and capacitor and electrode and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:21
-	0	6110531.pn. and (tantalum adj pentamethoxide) and capacitor and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:42
-	0	6110531.pn. and (tantalum adj pentamethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:42
-	0	5601869.pn. and (tantalum adj pentamethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:43
-	0	jp-05243524-\$.did. and (tantalum adj pentamethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 12:45
-	0	(tantalum adj pentamethoxide) and capacitor and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 14:19
-	0	438/240,250,253,393,399(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (tantulum adj pentamethoxide or tantulum adj pentaethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 16:06
-	0	438/240,250,253,393,399(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and ((tantulum adj pentamethoxide) or (tantulum adj pentaethoxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 15:51

-	0	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and ((tantalum adj pentamethoxide) or (tantulum adj pentaethoxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 15:52
-	1	(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and ((tantalum adj pentamethoxide) or (tantalum adj pentaethoxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 15:52
-	0	438/240,250,253,393,396,399(Ta or tantalum) and CVD and (capacitor) and (precursor) and (source adj gas) and (oxygen) and (dielectric) and (tantulum adj pentamethoxide or tantulum adj pentaethoxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/23 16:08
-	0	5919963.pn. and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/23 15:52
-	0	5919963.pn. and (precursor or absorption)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/23 16:23
-	1	20020025628.pn. and purging	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 11:45
-	0	20020025628.pn. and ((titanium adj nitride) or (tantalum adj nitride) or (tungsten adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 14:22
-	0	6203613.pn. and ((titanium adj nitride) or (tantalum adj nitride) or (tungsten adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 14:50
-	1	6203613.pn. and (flow rate or sccm)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 17:53
-	1	20020025628.pn. and (flow rate or sccm)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 14:53
-	147709	6203613.pn. and nitrogen or argon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 17:54
-	1	6203613.pn. and (nitrogen or argon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 17:56
-	1	6203613.pn. and (nitrogen or argon same inert)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/24 17:56
-	1	20020100959.pn. and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/27 10:16
-	0	20020100959.pn. and absorption	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/27 10:18
-	0	20020100959.pn. and (absorption or absorb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/27 10:19
-	0	6203613.pn. and (tantalum adj chloride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/27 12:14